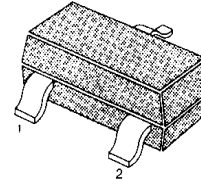


KST92/93**PNP EPITAXIAL SILICON TRANSISTOR****HIGH VOLTAGE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS (T_A=25 °C)**

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V _{CBO}	-300	V
:KST92		-200	V
:KST93			
Collector-Emitter Voltage	V _{CEO}	-300	V
:KST92		-200	V
:KST93			
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-500	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{STG}	150	°C
Thermal Resistance junction to Ambient	R _{TH(j-a)}	357	°C/w

• Refer to KSP92/93 for graphs

SOT-23



1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS (T_A=25 °C)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C = -100 μA, I _E =0	-300		V
:KST92			-200		V
:KST93					
*Collector -Emitter Breakdown Voltage	BV _{CEO}	I _C = -1mA, I _B =0	-300		V
:KST92			-200		V
:KST93					
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = -100 μA, I _C =0	-5		V
Collector Cut-off Current	I _{CBO}	V _{CB} = -200V, I _E =0		-0.25	μA
:KST92		V _{CB} = -160V, I _E =0		-0.25	μA
:KST93		V _{CE} =3V, I _C =0		-0.1	μA
Emitter Cut-off Current	I _{EBO}	V _{CE} = -10V, I _C = -1mA	25		
*DC Current Gain	h _{FE}	V _{CE} = -10V, I _C = -10mA	40		
		V _{CE} = -10V, I _C = -30mA	25		
*Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -20mA, I _B = -2mA		-0.5	V
*Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C = -20mA, I _B = -2mA		-0.9	V
Collector-Base Capacitance	C _{CB}	V _{CB} = -20V, I _E =0		6	pF
:KST92		f=1MHz		8	pF
:KST93					
Current Gain Bandwidth Product	f _T	V _{CE} = -20V, I _C = -10mA	50		MHz
		f=100MHz			

* Pulse Test: PW ≤ 300 μs, Duty Cycle ≤ 2%

MARKING CODE

TYPE	KST92	KST93
MARK	2D	2E

Marking